

Epitaxial growth and transport properties of Sr_2CrWO_6 thin films

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We report on the preparation and characterization of epitaxial thin films of the double-perovskite Sr_2CrWO_6 by Pulsed Laser Deposition (PLD). On substrates with low lattice mismatch like SrTiO_3 , epitaxial Sr_2CrWO_6 films with high crystalline quality can be grown in a molecular layer-by-layer growth mode. Due to the similar ionic radii of Cr and W, these elements show no sublattice order. Nevertheless, the measured Curie temperature is well above 400 K. Due to the reducing growth atmosphere required for double perovskites, the SrTiO_3 substrate surface undergoes an insulator-metal transition impeding the separation of thin film and substrate electric transport properties.

Double-perovskites of the form $\text{A}_2\text{BB}'\text{O}_6$ are interesting materials both due to their rich physics and their interesting properties with respect to applications in spin electronics. They are half metallic, i.e. have a high effective spin polarization at the Fermi level [1], and some compounds have a high Curie temperature T_C , e.g. $T_C = 635 \text{ K}$ in $\text{Sr}_2\text{CrReO}_6$ [2]. Large low field magnetoresistance effects are found in $\text{Sr}_2\text{FeMoO}_6$ [1, 3], $\text{Sr}_2\text{FeReO}_6$ [4] and Sr_2CrWO_6 [5]. Thin films of the well studied system $\text{Sr}_2\text{FeMoO}_6$ have been fabricated by pulsed-laser deposition (PLD) at relatively high temperatures of about 900 °C [6]. However, epitaxial growth was found to be complicated and difficult to control. There are indications that high structural quality of films grown on SrTiO_3 is associated with semiconducting behavior [7, 8]. Here, we report on the epitaxial growth of Sr_2CrWO_6 . Due to the good lattice match, epitaxial films of this material can be grown on SrTiO_3 substrates in a molecular layer-by-layer growth mode resulting in high crystalline quality.

Sr_2CrWO_6 thin films were deposited from stoichiometric targets [5] on atomically flat, HF etched and annealed (001) SrTiO_3 substrates by PLD using a 248 nm KrF excimer laser [9]. Fig. 1 shows the RHEED (Reflection High Energy Electron Diffraction) [10] intensity oscillations of the (0,0) diffraction spot recorded during the PLD growth of a *c*-axis oriented Sr_2CrWO_6 film. The molecular layer-by-layer or Frank-van der Merwe growth mode [11] is achieved for a substrate temperature of 740 °C, an argon pressure of $2 \cdot 10^{-4}$ Torr, a laser repetition rate of 2 Hz, and a laser energy density on the target of 1.2 J/cm^2 . RHEED was performed with 15 keV electrons at an incident angle of about 2° . To obtain the number of RHEED oscillations per unit cell, the film thickness has been determined precisely by X-ray reflectometry (Fig. 4) and then divided by the number of observed RHEED oscillations. The derived molecular layer or block thickness corresponds to half a unit cell ($c/2 = 4.004 \text{ \AA}$). Note that the intensity oscillations of the (0,0) and (0,1) spot are out of phase, since for the (0,1) spot the electrons reflected from different growth planes interfere constructively (in-Bragg condition). In this case no RHEED oscillations are expected. The fact that we do observe RHEED oscillations is caused by multiple and diffuse, incoherent scattering which results in an

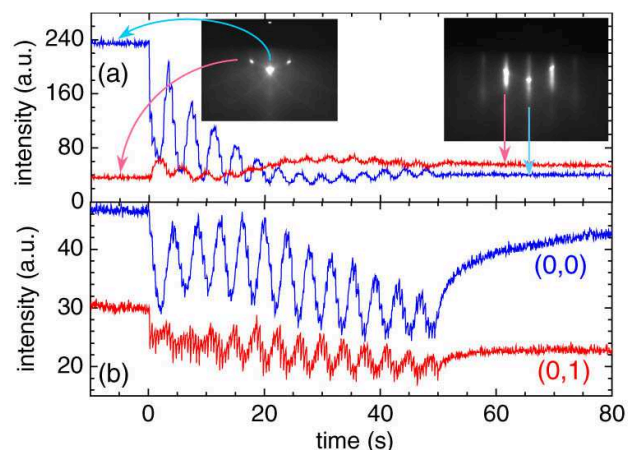


Figure 1: RHEED intensity oscillations observed during the growth of Sr_2CrWO_6 on (001) SrTiO_3 showing a clear π -shift between the (0,0) and (0,1) spot. (a) The first 100 pulses and (b) the second 100 pulses. In (b) the intensity of the (0,1) spot is shifted to lower values for clarity. The inset shows the RHEED patterns before deposition and after 100 pulses as indicated by the arrows.

increasing (decreasing) intensity with increasing (decreasing) step density [12, 13].

Figure 2 shows an *in situ* AFM picture of a 42 nm thick film. Clearly, a terrace structure due to the nonvanishing substrate miscut with about 4 \AA high steps corresponding to half a unit cell of Sr_2CrWO_6 can be seen. The AFM analysis shows that Sr_2CrWO_6 grows as an epitaxial film with a similar crystalline perfection and very smooth surface as the doped manganites [9, 14].

As shown in the inset of Fig. 3, within the resolution of our four circle x-ray diffractometer only (00 γ) peaks ($\gamma = 2; 4; 6; \dots$) could be detected. Rocking curves of the (004) peak had a full width at half maximum (FWHM) of only 0.025° which is very close to the FWHM of the substrate peak. The fact that Laue oscillations were detected around the film diffraction peaks (Fig. 3) indicates that the strain due to lattice mismatch between film and substrate ($\epsilon = 0.1\%$ for SrTiO_3) is not relaxed, i.e. the films grow coherently strained. The unit cell of the high quality strained films has a tetragonal distortion and is slightly larger than the bulk unit cell ($a_{\text{bulk}} = c_{\text{bulk}} = 7.813 \text{ \AA}$, $a_{\text{film}} = 2 \cdot a_{\text{SrTiO}_3} = 7.810 \text{ \AA}$ and $c_{\text{film}} = 8.005 \text{ \AA}$). Fig. 4

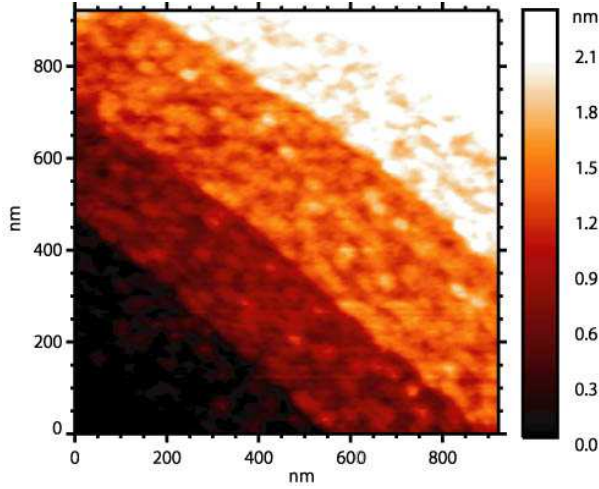


Figure 2: AFM image of a 42 nm thick epitaxial Sr_2CrWO_6 film grown on a HF-etched (001) SrTiO_3 substrate

shows X-ray reflectometry data of a 52 nm thick Sr_2CrWO_6 film on a SrTiO_3 substrate. Fitting the data [15] gives a film thickness that agrees to that obtained from counting the RHEED oscillations to within less than 3%. Note that the quality of the fit is extraordinary good.

We have also grown epitaxial Sr_2CrWO_6 thin films on other substrates such as NdGaO_3 , MgAlO_4 and LaAlO_3 . On these substrates a much rougher surface and a more distorted crystal structure is obtained. This is caused by the larger lattice mismatch of these substrates to Sr_2CrWO_6 as compared to SrTiO_3 .

An important parameter of the double perovskites is the sublattice order of the B and B^0 ions (in our case Cr and W). It is evident that for perfect order a superstructure is obtained resulting in a (111) peak in the x-ray diffraction. The intensity of the (111) peak can therefore be used as a quantitative measure of the sublattice order of the B , B^0 ions. In our Sr_2CrWO_6 thin films no such peak is found within the experimental resolution for films grown on (001) or (111) SrTiO_3 , (110) NdGaO_3 , (001) MgAlO_4 and (001) LaAlO_3 . This gives strong evidence that for our epitaxial Sr_2CrWO_6 films with high crystalline quality no Cr,W sublattice order is established. It is likely that this is caused by the very similar ionic radii of Cr and W resulting in a very small gain of structural energy by ionic order. We note, however, that despite the complete disorder of the B and B^0 ions a Curie temperature well above 400 K is obtained. This raises questions about theoretical models requiring sublattice order for high T_C . The saturation magnetization M_S was found to strongly depend on the growth conditions and the substrate material. A maximum value of $M_S = 1.9 \mu_B/\text{f.u.}$ at 5 K was obtained for a 48 nm thick film grown on (111) SrTiO_3 at 780 C.

Resistance vs. temperature was measured with a standard four probe configuration. All films not grown on SrTiO_3 substrates show semiconducting behavior what might be attributed to the large lattice mismatch. We note however, the double perovskite films like Sr_2CrWO_6 or Sr_2FeMo_6 are grown under very low oxygen partial pressure [6, 8], vacuum

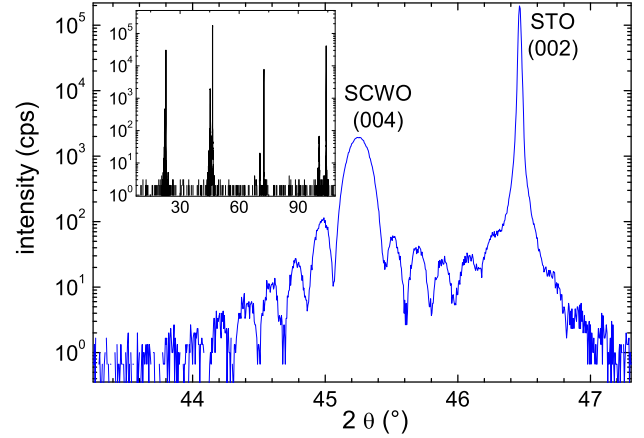


Figure 3: θ - 2θ scan showing the (004) peak of a Sr_2CrWO_6 film with the Laue oscillations and the (002) peak of the SrTiO_3 substrate. The inset shows the θ - 2θ scan from 30 to 90 .

[7] or Argon atmosphere [5, 8, 16] in a temperature range between 700 and 900 C. Under these conditions (e.g. $T = 800$ C, $p_{\text{O}_2} = 1 \cdot 10^{-8}$ Torr) the surface of the SrTiO_3 substrates becomes oxygen deficient within a few minutes. That is, a few μm thick, oxygen deficient surface layer ($\text{SrTiO}_{3-\delta}$) is obtained resulting in a conducting substrate surface [17]. This process is further supported by the reducing plasma during the PLD process. We found that the resistance of the SrTiO_3 substrate depends strongly on temperature, reducing atmosphere and time. In Fig. 5, the $R(T)$ curve of a SrTiO_3 substrate annealed at 820 in Ar is shown as a reference. After the treatment the substrate turns black and shows metallic behavior.

Fig. 5 also shows the $R(T)$ curve of a Sr_2CrWO_6 film grown at a low substrate temperature of only 740 C. Evidently, whether or not the metallic behavior results from the film or the substrate, we have etched trenches into the film (see inset in Fig. 5) interrupting the film and forcing the measurement current to flow in parts through the SrTiO_3 substrate. As can be seen in Fig. 5 the resistance is still metallic above

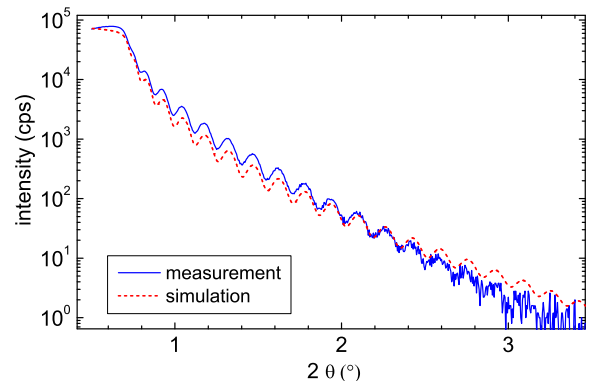


Figure 4: X-ray reflectometry data (solid line) and simulation data (broken line) [15].

50 K but has been increased significantly by roughly one order of magnitude. However, this difference cannot be unambiguously attributed to the interruption of the Sr_2CrWO_6 film alone because the trenches are deeper than the film thickness, i.e. the outermost layers of the SrTiO_3 which may be well conducting are also cut from the current path. Hence, for the Sr_2CrWO_6 films on SrTiO_3 we only have some indication that these films are metallic, however, we cannot definitely prove it at present. Due to the problems of conducting substrate surfaces, in Fig. 5 we plot the resistance of the sample configuration given in the inset and do not plot the resistivity.

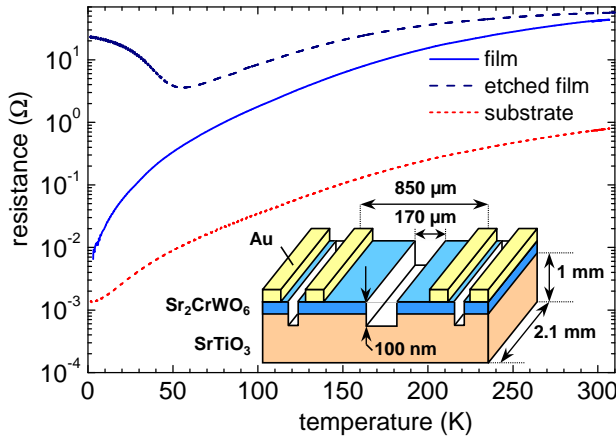


Figure 5: Resistance versus temperature for a 50 nm thick Sr_2CrWO_6 film grown at 740 C (solid line). The inset shows the sample geometry. The dashed line represents the $R(T)$ curve of the same film after etching a 100 nm deep and 170 μm wide trench to interrupt the Sr_2CrWO_6 film. As a reference, the dotted curve shows the $R(T)$ curve of a SrTiO_3 substrate annealed at 820 C in Ar.

In summary, we have grown epitaxial Sr_2CrWO_6 thin films with very high crystalline quality on SrTiO_3 by PLD. Since the ionic radii of Cr and W are almost identical, no sublattice order of these elements is achieved. Nevertheless, we observe Curie temperatures well above 400 K for these disordered films. The transport properties of the Sr_2CrWO_6 films on SrTiO_3 could not unambiguously be separated from those of the substrate, since the SrTiO_3 substrate is turned metallic under the reducing deposition conditions.

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